

2SC5628

Silicon NPN Epitaxial
High Frequency Amplifier / Oscillator

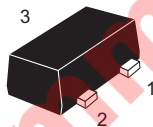
REJ03G0750-0300
(Previous ADE-208-979A)
Rev.3.00
Aug.10.2005

Features

- Super compact package;
(1.4 × 0.8 × 0.59mm)
- High power gain and low noise figure;
(PG = 9 dB, NF = 1.1 dB typ, at f = 900 MHz, V_{CE} = 1 V)

Outline

RENESAS Package code: PUSF0003ZA-A
(Package name: MFPAK[®])



1. Emitter
2. Base
3. Collector

Note: Marking is "XZ-".

*MFPAK is a trademark of Renesas Technology Corp.

Absolute Maximum Ratings

(T_a = 25°C)

| Item | Symbol | Ratings | Unit |
|------------------------------|------------------|-------------|------|
| Collector to base voltage | V _{CBO} | 15 | V |
| Collector to emitter voltage | V _{CEO} | 8 | V |
| Emitter to base voltage | V _{EBO} | 1.5 | V |
| Collector current | I _C | 50 | mA |
| Collector power dissipation | P _C | 80 | mW |
| Junction temperature | T _J | 150 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °C |

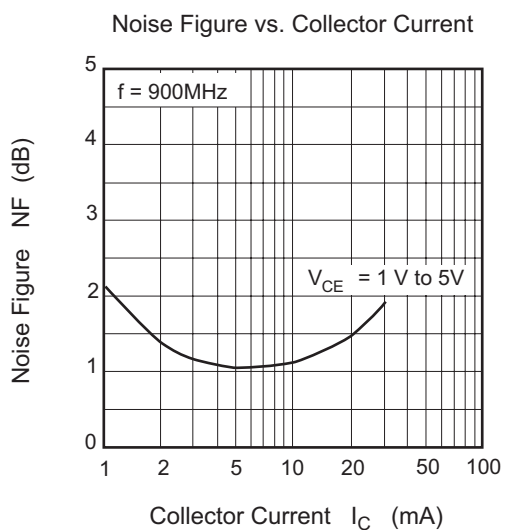
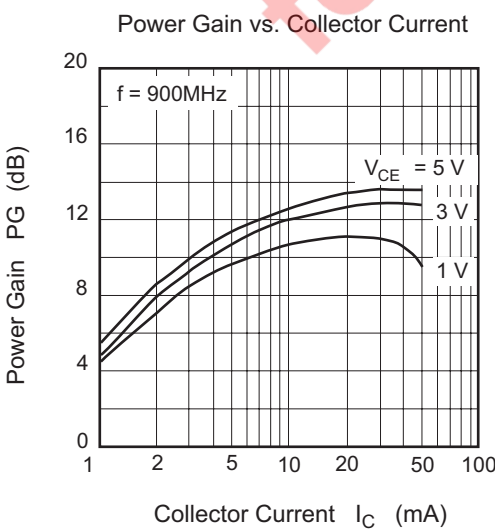
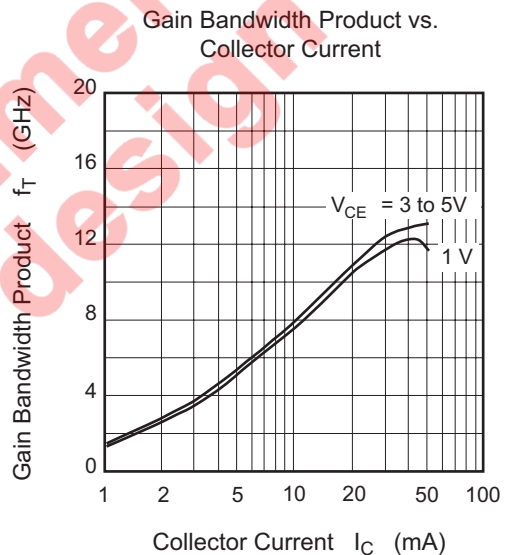
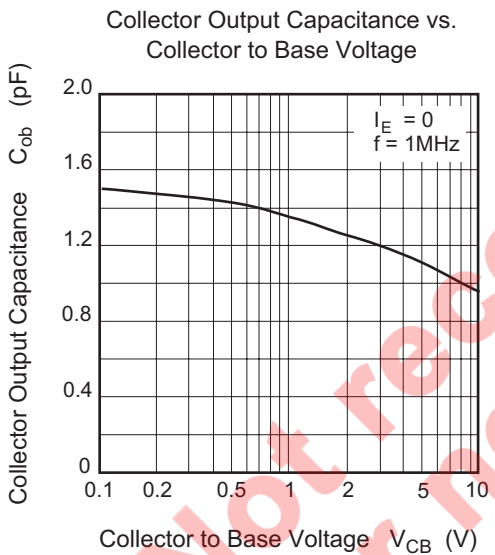
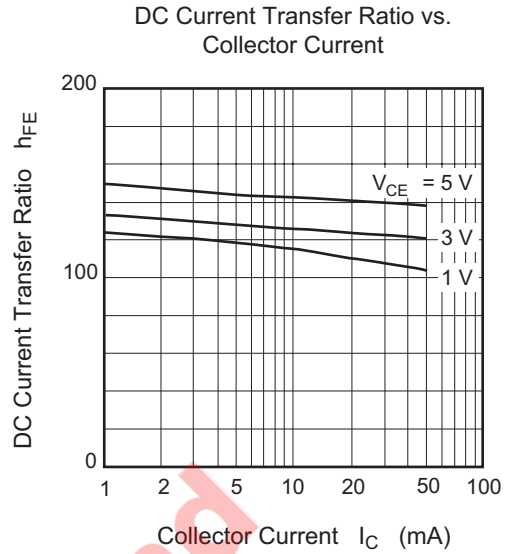
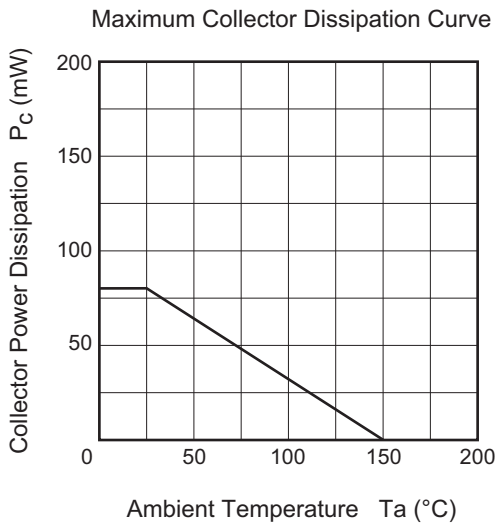
Electrical Characteristics

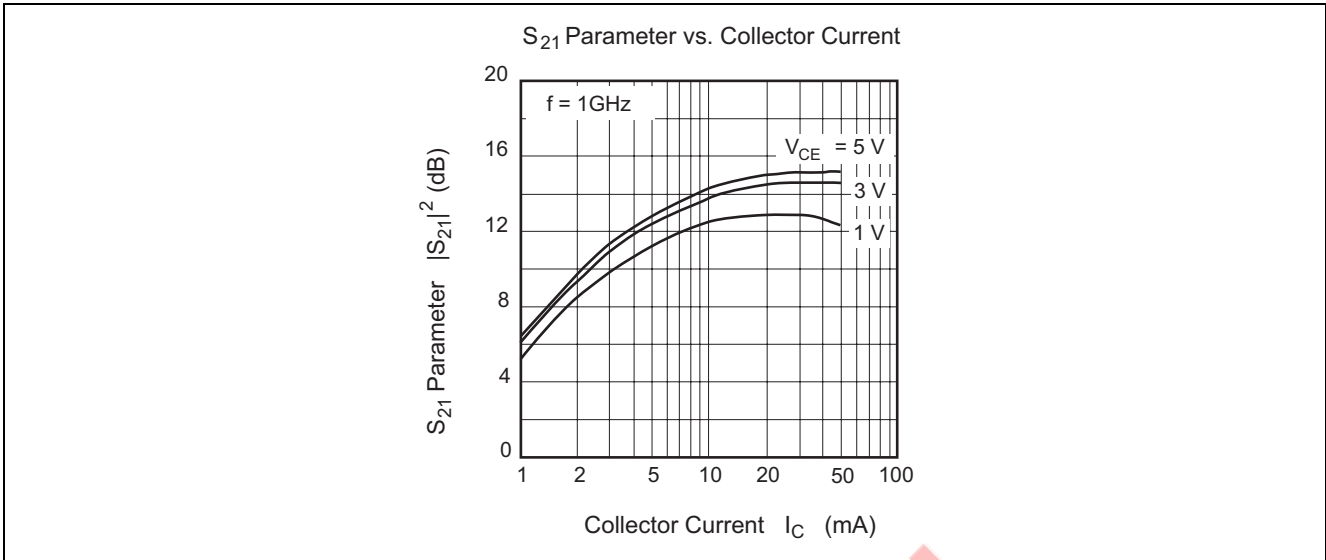
(Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test Conditions |
|-------------------------------------|---------------|-----|------|------|---------|--|
| Collector to base breakdown voltage | $V_{(BR)CBO}$ | 15 | — | — | V | $I_C = 10\mu A, I_E = 0$ |
| Collector cutoff current | I_{CBO} | — | — | 0.2 | μA | $V_{CB} = 12V, I_E = 0$ |
| Collector cutoff current | I_{CEO} | — | — | 1 | μA | $V_{CE} = 8V, R_{BE} = \infty$ |
| Emitter cutoff current | I_{EBO} | — | — | 1 | μA | $V_{EB} = 1.5V, I_C = 0$ |
| DC current transfer ratio | h_{FE} | 80 | 100 | 160 | | $V_{CE} = 1V, I_C = 5mA$ |
| Collector output capacitance | C_{ob} | — | 0.55 | 0.85 | pF | $V_{CB} = 1V, I_E = 0$ $f = 1MHz$ |
| Gain bandwidth product | f_T | 6 | 9 | — | GHz | $V_{CE} = 1V, I_C = 5mA$ |
| Power gain | PG | 11 | 14 | — | dB | $V_{CE} = 1V, I_C = 5mA$ $f = 900MHz$ |
| Noise figure | NF | — | 1.1 | 2.0 | dB | $V_{CE} = 1V, I_C = 5mA$ $f = 900MHz$ |

Not recommend
for new design

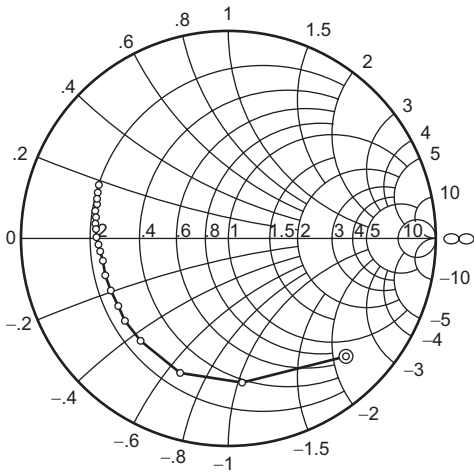
Main Characteristics





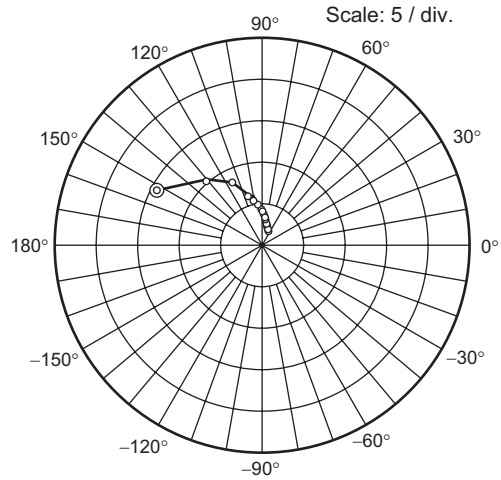
Not recommended for new design

S11 Parameter vs. Frequency



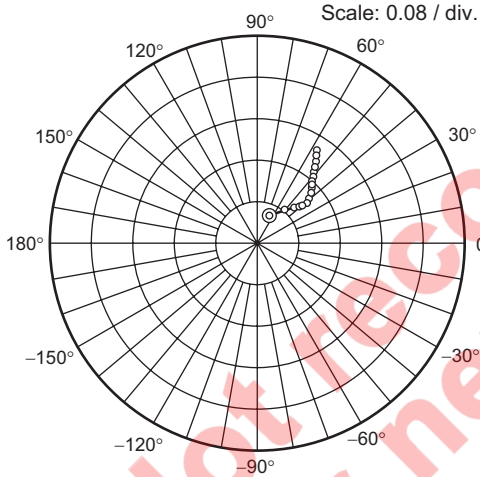
Condition : $V_{CE} = 1\text{ V}$, $I_C = 5\text{ mA}$
 100 to 2000 MHz (100 MHz step)
 ⊙ — ○

S21 Parameter vs. Frequency



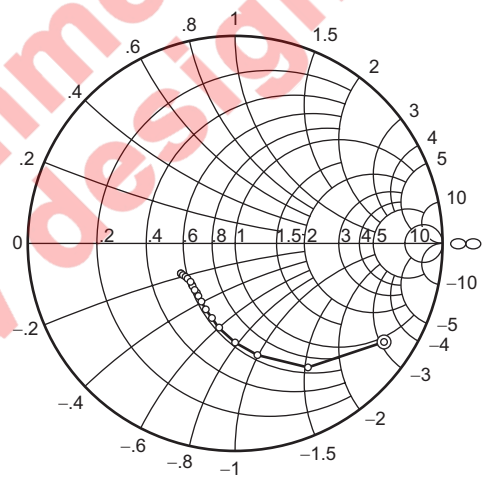
Condition : $V_{CE} = 1\text{ V}$, $I_C = 5\text{ mA}$
 100 to 2000 MHz (100 MHz step)
 ⊙ — ○

S12 Parameter vs. Frequency



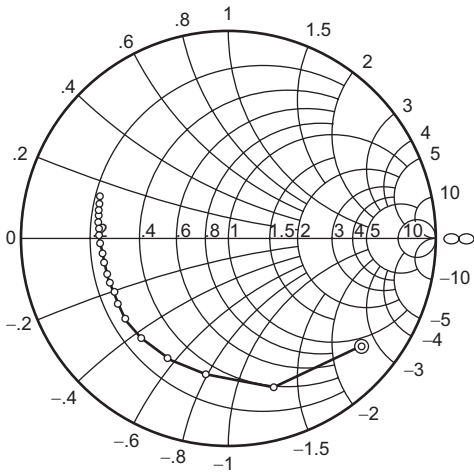
Condition : $V_{CE} = 1\text{ V}$, $I_C = 5\text{ mA}$
 100 to 2000 MHz (100 MHz step)
 ⊙ — ○

S22 Parameter vs. Frequency



Condition : $V_{CE} = 1\text{ V}$, $I_C = 5\text{ mA}$
 100 to 2000 MHz (100 MHz step)
 ⊙ — ○

S11 Parameter vs. Frequency

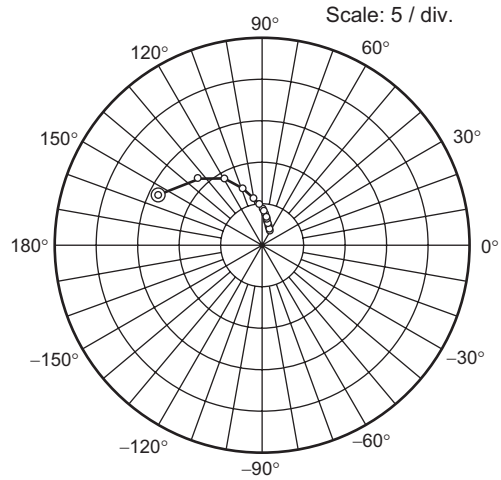


Condition : $V_{CE} = 3\text{ V}$, $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)



S21 Parameter vs. Frequency

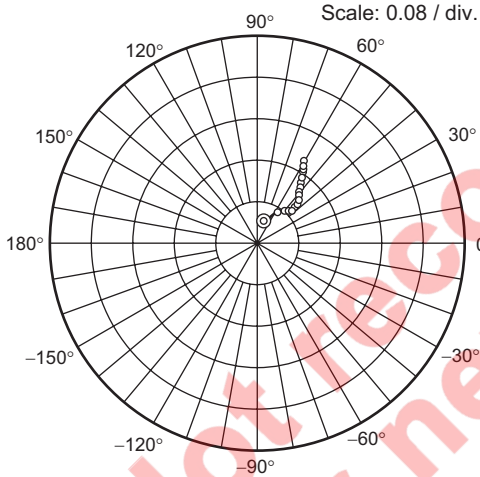


Condition : $V_{CE} = 3\text{ V}$, $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)



S12 Parameter vs. Frequency

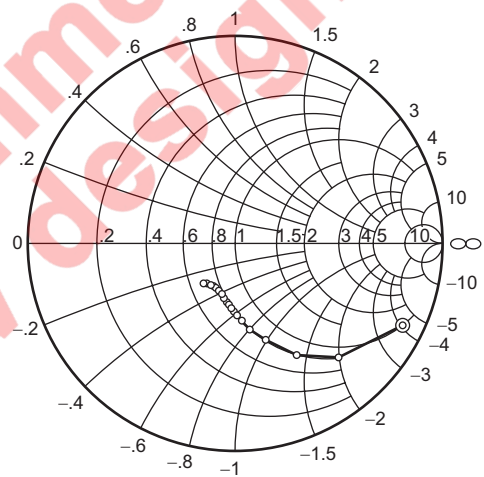


Condition : $V_{CE} = 3\text{ V}$, $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)



S22 Parameter vs. Frequency



Condition : $V_{CE} = 3\text{ V}$, $I_C = 5\text{ mA}$

100 to 2000 MHz (100 MHz step)



Sparameter

 $(V_{CE} = 1V, I_C = 5mA, Z_o = 50\Omega)$

| f (MHz) | S11 | | S21 | | S12 | | S22 | |
|---------|-------|--------|-------|-------|--------|------|-------|--------|
| | MAG | ANG | MAG | ANG | MAG | ANG | MAG | ANG |
| 100 | 0.815 | -46.1 | 13.63 | 152.2 | 0.0509 | 67.0 | 0.882 | -32.5 |
| 200 | 0.734 | -84.6 | 10.68 | 130.6 | 0.0834 | 51.0 | 0.695 | -58.5 |
| 300 | 0.692 | -111.2 | 8.23 | 116.8 | 0.0998 | 42.9 | 0.550 | -76.0 |
| 400 | 0.665 | -127.4 | 6.58 | 107.9 | 0.108 | 39.5 | 0.459 | -88.5 |
| 500 | 0.650 | -139.6 | 5.44 | 101.4 | 0.114 | 38.0 | 0.399 | -98.1 |
| 600 | 0.644 | -148.8 | 4.61 | 96.3 | 0.120 | 38.3 | 0.360 | -105.7 |
| 700 | 0.640 | -155.6 | 4.03 | 92.2 | 0.124 | 39.0 | 0.333 | -112.2 |
| 800 | 0.641 | -161.6 | 3.56 | 88.6 | 0.128 | 39.9 | 0.315 | -117.8 |
| 900 | 0.638 | -166.9 | 3.20 | 85.3 | 0.134 | 41.8 | 0.301 | -122.4 |
| 1000 | 0.638 | -171.6 | 2.90 | 82.2 | 0.138 | 43.5 | 0.292 | -126.7 |
| 1100 | 0.643 | -175.1 | 2.66 | 79.6 | 0.143 | 44.4 | 0.286 | -130.2 |
| 1200 | 0.643 | -178.5 | 2.46 | 77.2 | 0.149 | 46.2 | 0.280 | -133.6 |
| 1300 | 0.648 | 178.5 | 2.28 | 74.9 | 0.154 | 47.8 | 0.279 | -135.6 |
| 1400 | 0.651 | 175.4 | 2.15 | 72.8 | 0.161 | 49.1 | 0.278 | -138.6 |
| 1500 | 0.658 | 173.2 | 2.03 | 70.5 | 0.168 | 50.9 | 0.277 | -140.9 |
| 1600 | 0.663 | 170.0 | 1.92 | 68.5 | 0.174 | 51.8 | 0.279 | -143.3 |
| 1700 | 0.667 | 167.2 | 1.82 | 66.7 | 0.182 | 53.2 | 0.281 | -145.0 |
| 1800 | 0.669 | 165.0 | 1.74 | 64.4 | 0.189 | 54.6 | 0.282 | -147.1 |
| 1900 | 0.673 | 163.1 | 1.67 | 63.2 | 0.196 | 55.5 | 0.286 | -149.3 |
| 2000 | 0.682 | 161.0 | 1.60 | 61.4 | 0.204 | 56.4 | 0.289 | -150.6 |

Not recommended
for new designs

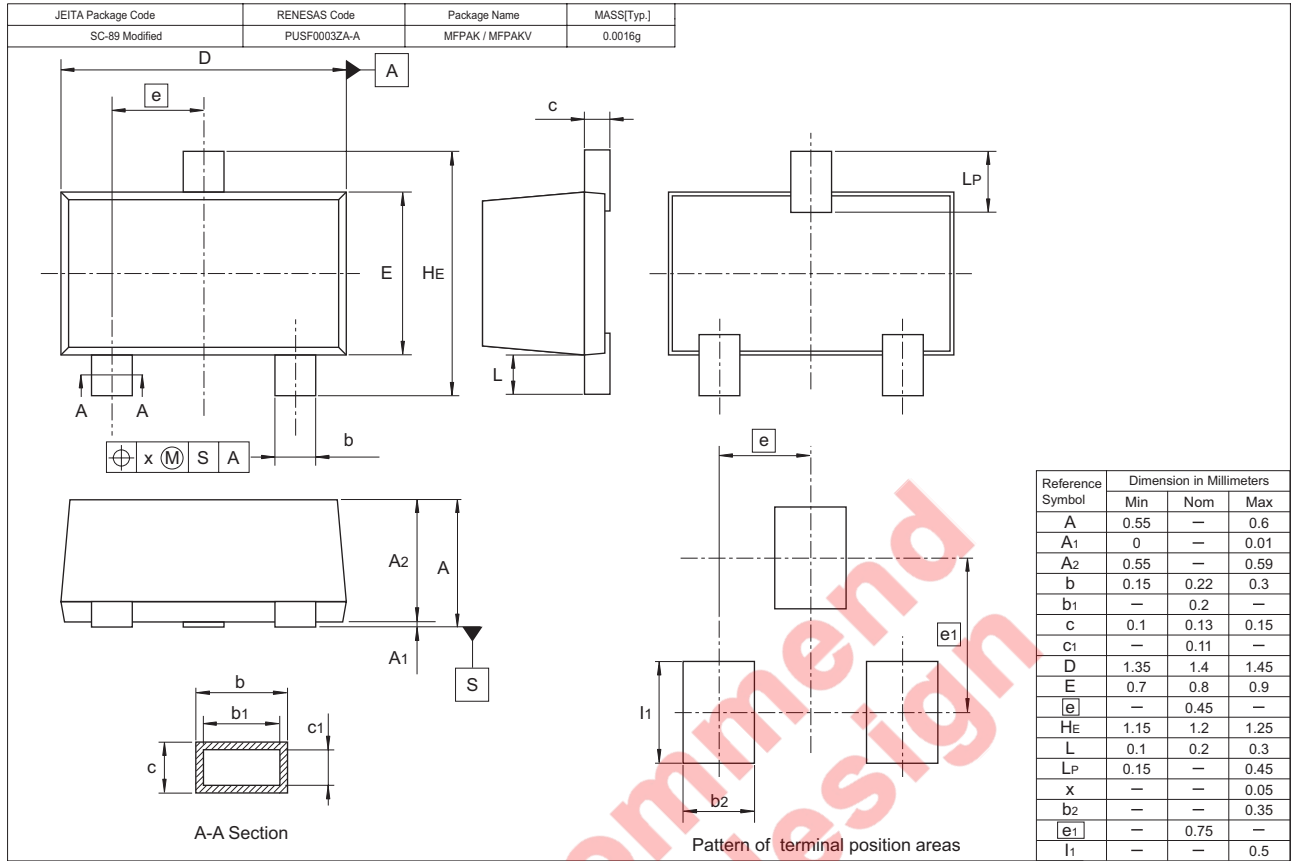
Sparameter

 $(V_{CE} = 3V, I_C = 5mA, Z_o = 50\Omega)$

| f (MHz) | S11 | | S21 | | S12 | | S22 | |
|---------|-------|--------|-------|-------|--------|------|-------|--------|
| | MAG | ANG | MAG | ANG | MAG | ANG | MAG | ANG |
| 100 | 0.826 | -39.3 | 14.04 | 155.5 | 0.0412 | 69.9 | 0.906 | -25.8 |
| 200 | 0.746 | -74.6 | 11.47 | 134.9 | 0.0700 | 54.9 | 0.738 | -47.3 |
| 300 | 0.685 | -100.5 | 9.14 | 121.1 | 0.0864 | 46.7 | 0.591 | -61.9 |
| 400 | 0.646 | -117.4 | 7.41 | 111.9 | 0.0950 | 43.0 | 0.490 | -71.9 |
| 500 | 0.627 | -130.7 | 6.19 | 104.8 | 0.101 | 41.3 | 0.419 | -79.9 |
| 600 | 0.617 | -141.0 | 5.27 | 99.6 | 0.107 | 41.3 | 0.369 | -85.7 |
| 700 | 0.606 | -149.0 | 4.61 | 95.0 | 0.111 | 41.6 | 0.333 | -90.7 |
| 800 | 0.598 | -155.4 | 4.09 | 91.6 | 0.115 | 42.5 | 0.307 | -95.3 |
| 900 | 0.605 | -161.3 | 3.67 | 87.7 | 0.120 | 44.3 | 0.287 | -99.0 |
| 1000 | 0.604 | -166.1 | 3.35 | 84.7 | 0.124 | 45.6 | 0.273 | -102.6 |
| 1100 | 0.604 | -170.6 | 3.06 | 81.8 | 0.129 | 46.8 | 0.262 | -106.0 |
| 1200 | 0.607 | -174.2 | 2.83 | 79.5 | 0.134 | 49.0 | 0.253 | -108.8 |
| 1300 | 0.605 | -178.2 | 2.62 | 77.1 | 0.139 | 50.4 | 0.249 | -111.0 |
| 1400 | 0.608 | 178.9 | 2.47 | 74.9 | 0.145 | 51.9 | 0.245 | -114.3 |
| 1500 | 0.618 | 175.5 | 2.32 | 72.7 | 0.152 | 53.4 | 0.242 | -116.6 |
| 1600 | 0.622 | 172.4 | 2.19 | 70.7 | 0.157 | 54.8 | 0.241 | -118.9 |
| 1700 | 0.627 | 170.0 | 2.08 | 68.9 | 0.164 | 56.2 | 0.241 | -121.3 |
| 1800 | 0.629 | 166.9 | 1.99 | 66.7 | 0.171 | 57.6 | 0.242 | -123.4 |
| 1900 | 0.633 | 164.3 | 1.90 | 65.2 | 0.177 | 58.7 | 0.243 | -125.9 |
| 2000 | 0.641 | 162.3 | 1.82 | 63.4 | 0.186 | 59.5 | 0.245 | -127.7 |

Not recommended for new designs

Package Dimensions



Ordering Information

| Part Name | Quantity | Shipping Container |
|----------------|----------|-----------------------------------|
| 2SC5628XZ-TL-E | 9000 | φ 178 mm Reel, 8 mm Emboss Taping |

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510